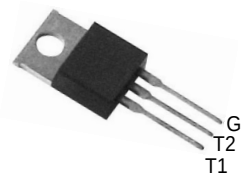
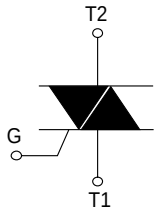
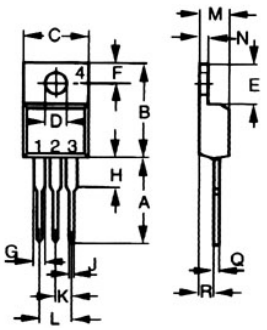
JSMICRO SEMICONDUCTOR

BTA08-600B





Dimensions TO-220



Dim.	Inches		Milimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.550	12.70	13.97
B	0.580	0.630	14.73	16.00
C	0.390	0.420	9.91	10.66
D	0.139	0.161	3.54	4.08
E	0.230	0.270	5.85	6.85
F	0.100	0.125	2.54	3.18
G	0.045	0.065	1.15	1.65
H	0.110	0.230	2.79	5.84
J	0.025	0.040	0.64	1.01
K	0.100	BSC	2.54	BSC
M	0.170	0.190	4.32	4.82
N	0.045	0.055	1.14	1.39
Q	0.014	0.022	0.35	0.56
R	0.090	0.110	2.29	2.79

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-220AB	Tc = 110°C	8	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, Tj initial = 25°C)	F = 60 Hz	t = 16.7 ms	84	A
		F = 50 Hz	t = 20 ms	80	
I^2t	I^2t Value for fusing	tp = 10 ms		36	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT} , tr ≤ 100 ns	F = 120 Hz	Tj = 125°C	50	A/µs
I_{GM}	Peak gate current	tp = 20 µs	Tj = 125°C	4	A
$P_{G(AV)}$	Average gate power dissipation		Tj = 125°C	1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise specified)

■ SNUBBERLESS™ and LOGIC LEVEL(3 Quadrants)

Symbol	Test Conditions	Quadrant		BTA/BTB		Unit
				CW	BW	
I_{GT} (1)	V_D = 12 V R_L = 30 Ω	I - II - III	MAX.	35	50	mA
V_{GT}		I - II - III	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ R_L = 3.3 kΩ Tj = 125°C	I - II - III	MIN.	0.2		V
I_H (2)	I_T = 100 mA		MAX.	35	50	mA
I_L	I_G = 1.2 I_{GT}	I - III	MAX.	50	70	mA
		II		60	80	
dV/dt (2)	V_D = 67 % V_{DRM} gate open Tj = 125°C		MIN.	400	1000	V/µs
(dI/dt)c (2)	Without snubber Tj = 125°C		MIN.	4.5	7	A/ms

Symbol	Test Conditions	Quadrant		Value	Unit
I_{GT} (1)	V_D = 12 V R_L = 30 Ω	I - II - III IV	MAX.	50 100	mA
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ R_L = 3.3 Ω Tj = 125°C	ALL	MIN.	0.2	V
I_H (2)	I_T = 500 mA		MAX.	50	mA
I_L	$I_G = 1.2\ I_{GT}$	I - III - IV	MAX.	50	mA
		II		100	
dV/dt (2)	V_D = 67 % V_{DRM} gate open Tj = 125°C		MIN.	400	V/µs
(dV/dt)c (2)	(dI/dt)c =3.5 A/ms Tj = 125°C		MIN.	10	V/µs

STATIC CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
V_{TM} (2)	I_{TM} = 11 A tp = 380 µs	Tj = 25°C	MAX.	1.55	V
V_{to} (2)	Threshold voltage	Tj = 125°C	MAX.	0.85	V
R_d (2)	Dynamic resistance	Tj = 125°C	MAX.	50	mΩ
I_{DRM}	$V_{DRM} = V_{RRM}$	Tj = 25°C	MAX.	5	µA
I_{RRM}		Tj = 125°C		1	mA

Note 1: minimum IGT is guaranted at 5% of IGT max.

Note 2: for both polarities of A2 referenced to A1

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	1.6	°C/W
$R_{th(j-a)}$	Junction to ambient	60	°C/W

PRODUCT SELECTOR

Part Number	Voltage (xxx)		Sensitivity	Type	Package
	200 V ~~ 1000 V				
BTB/BTA08	X	X	50 mA	Standard	TO-220AB

OTHER INFORMATION

Part Number	Marking	Weight	Base quantity	Packing mode
BTB/BTA08	BTB/BTA08	2.3 g	250	Bulk

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

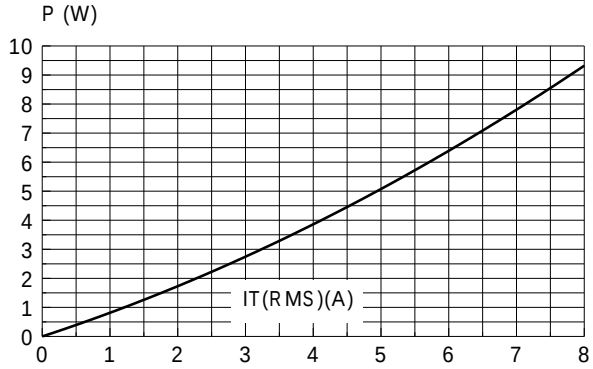


Fig. 2-1: RMS on-state current versus case temperature (full cycle).

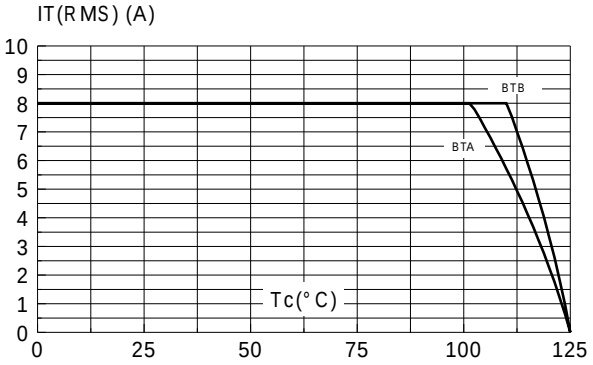


Fig. 2-2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm),full cycle.

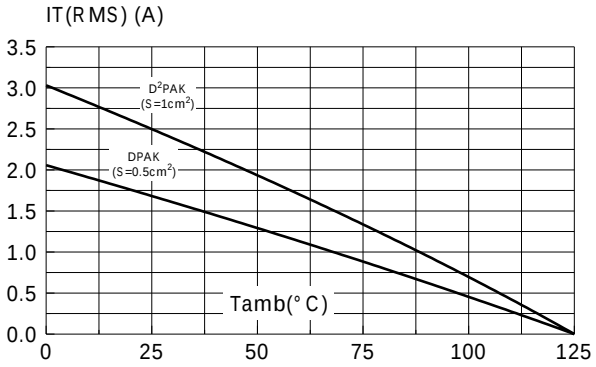


Fig. 3: Relative variation of thermal impedance versus pulse duration.

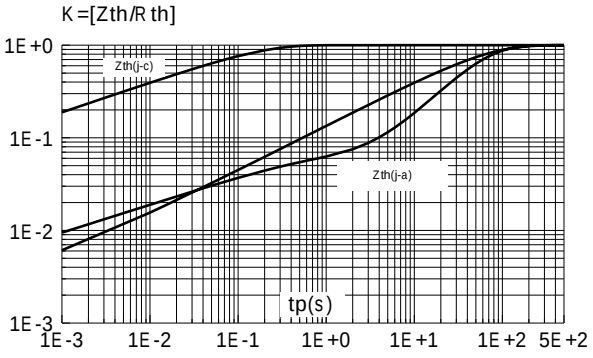


Fig. 4: On-state characteristics (maximum values).

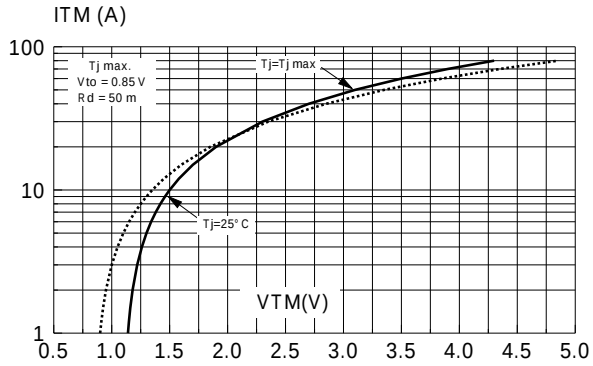


Fig. 5: Surge peak on-state current versus number of cycles.

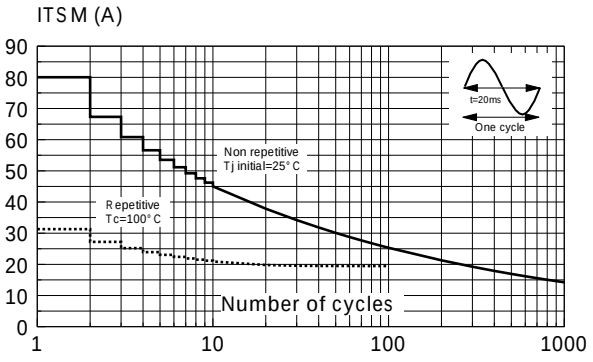


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I^2t.

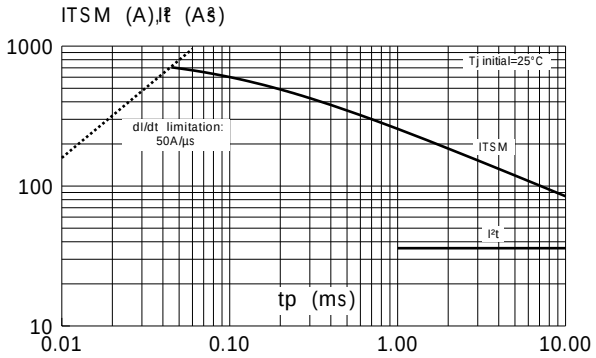


Fig. 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

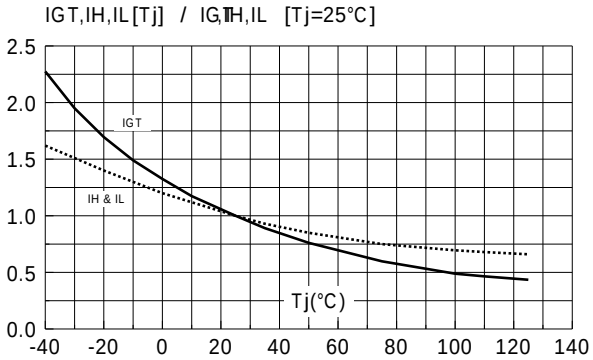


Fig. 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values). Standard Types

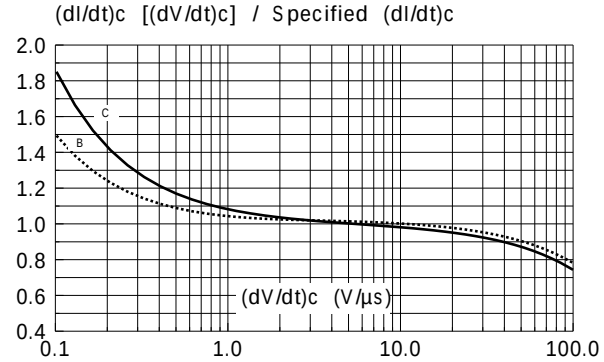


Fig. 9: Relative variation of critical rate of decrease of main current versus junction temperature.

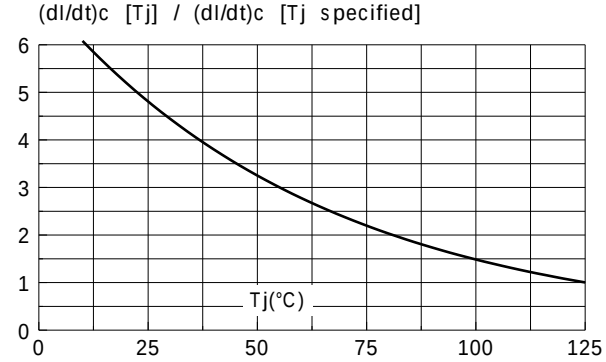


Fig. 10: DPAK and D^2PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 µm).

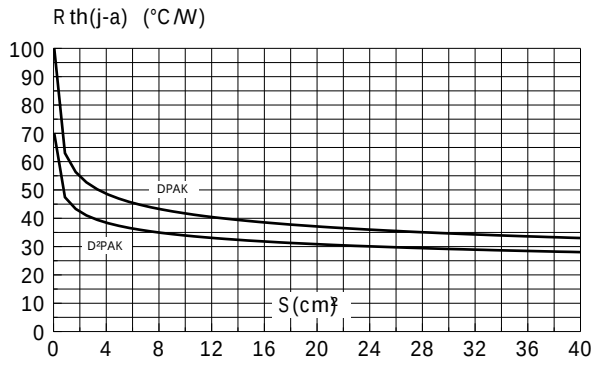


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I²t.

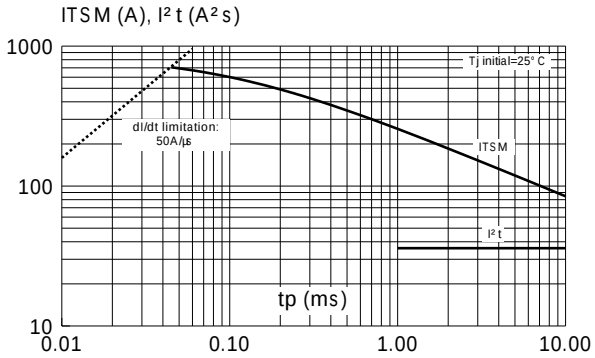


Fig. 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

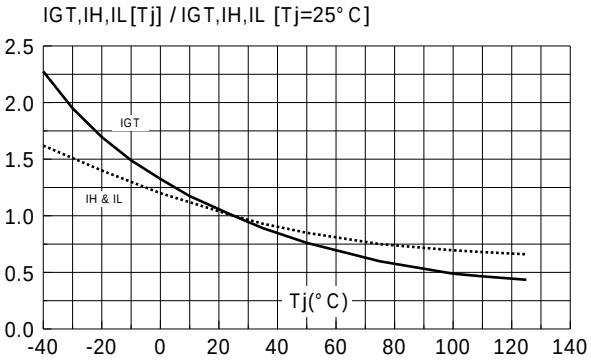


Fig. 8-1: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values). Snubberless & Logic Level Types

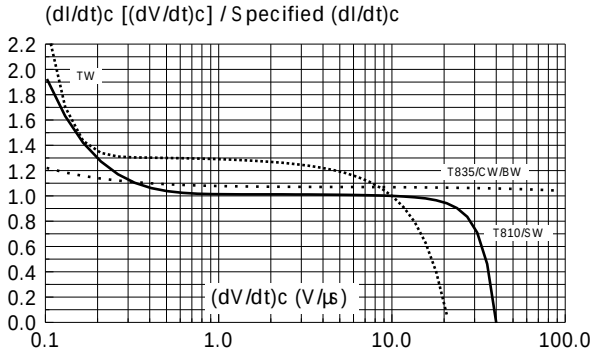


Fig. 8-2: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values). Standard Types

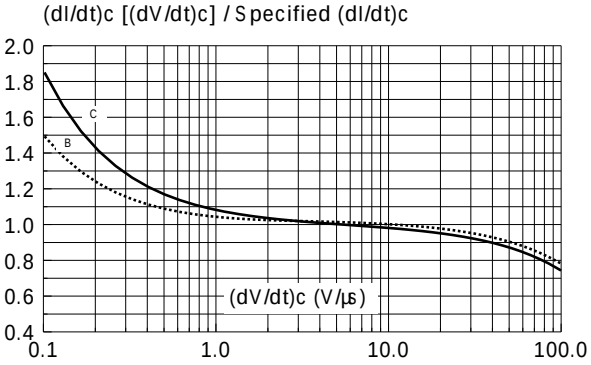
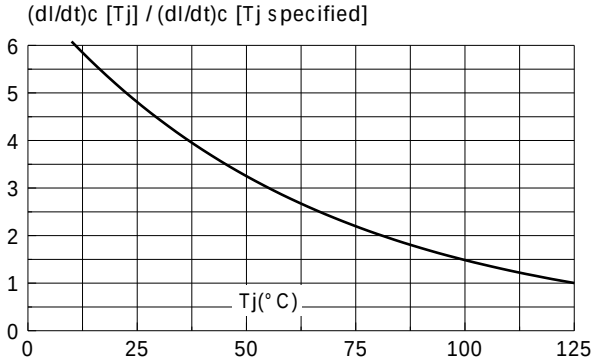


Fig. 9: Relative variation of critical rate of decrease of main current versus junction temperature.



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